

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

FARHAD K. MOGHADAM et al.

Application No.: Unassigned

Filed: Herewith

For: SEQUENTIAL GAS FLOW OXIDE
DEPOSITION TECHNIQUE

Examiner: Unassigned

Art Unit: Unassigned

INFORMATION DISCLOSURE
STATEMENT UNDER 37 CFR §1.97 and
§1.98

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

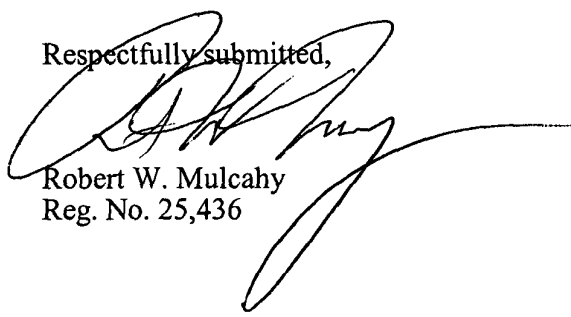
The references cited on attached form PTO/SB/08A and PTO/SB/08B are being called to the attention of the Examiner. Copies of the references are enclosed. It is respectfully requested that the cited references be expressly considered during the prosecution of this application, and the references be made of record therein and appear among the "references cited" on any patent to issue therefrom.

As provided for by 37 CFR 1.97(g) and (h), no representation is being made that a search has been conducted or that this statement encompasses all the possible relevant information, and no inference should be made that the information and references cited are, or are considered to be material to patentability because they are in this statement. No inference should be made that the information and references cited are prior art merely because they are in this statement.

Applicant believes that no fee is required for submission of this statement.

However, if a fee is required, the Commissioner is authorized to deduct such fee from the undersigned's Deposit Account No. 20-1430. Please deduct any additional fees from, or credit any overpayment to, the above-noted Deposit Account.

Respectfully submitted,



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Substitute for form 1449/PTO

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Filing Date	Filed Herewith
First Named Inventor	Moghadam, Farhad K., et. al.
Art Unit	Unassigned
Examiner Name	Unassigned
Attorney Docket Number	A7632/T49100

[illegible]

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)				
	AM	WO	01/40541	A1	06-07-2001			<input type="checkbox"/>
	AN	WO	00/61833	A1	10-19-2000			<input type="checkbox"/>
	AO	WO	01/66832	A2	09-13-2001			<input type="checkbox"/>
	AP	WO	00/54320	A1	09-14-2000			<input type="checkbox"/>
	AQ	EP	526 779	B1	02-10-1993			<input type="checkbox"/>
	AR	EP	442 490	A1	08-21-1991			<input type="checkbox"/>
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**Examiner
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¹ **Applicant's** unique citation designation number (optional). ² Kind Codes of U.S. Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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Complete if Known

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NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	AS	"Atomic Layer Deposition" by Physical Inorganic Chemistry, Institute of Applied Synthetic Chemistry, downloaded from website http://www.ias.tuwien.ac.at/research/fghh/research/pic_research_ald.html on 7/23/02	
	AT	GEORGE et al., "Atomic layer controlled deposition of SiO ₂ and Al ₂ O ₃ using ABAB... binary reaction sequence chemistry," <i>Applied Surface Science</i> , 82/83:460-467 (1994).	
	AU	GEORGE et al., "Surface Chemistry for Atomic Layer Growth," <i>J. Phys. Chem.</i> , 100(31):13121-13131 (1996).	
	AV	KLAUS et al., "Atomic Layer Deposition of SiO ₂ Using Catalyzed and Uncatalyzed Self-Limiting Surface Reactions," <i>Surface Review and Letters</i> , 6(3/4):435-448 (1999).	
	AW	KLAUS et al., "Atomic layer controlled growth of SiO ₂ films using binary reaction sequence chemistry," <i>Appl. Phys. Lett.</i> , 70(9):1092-1094 (1997).	
	AX	MORISHITA et al., "New substances for atomic-layer deposition of silicon dioxide," <i>J. Non-Crystalline Solids</i> , 187:66-69 (1995).	
	AY	WISE et al., "Diethyldiethoxysilane as a New Precursor for SiO ₂ Growth on Silicon," from <i>Gas-Phase and Surface Chemistry in electronic Materials Processing</i> , Mountziaris et al., eds., from Symposium held 11/29/93 thru 12/2/93 in Boston Massachusetts, pages 37-43.	
	AZ	YAMAGUCHI et al., "Atomic-layer chemical-vapor-deposition of silicon dioxide films with an extremely low hydrogen content," <i>Applied Surface Science</i> , 130-132:202-207 (1998).	

Examiner
SignatureDate
Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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